

WHAT IS CLAIMED IS:

1. A semiconductor device comprising;  
a semiconductor chip,  
5 a protective insulating layer covering the surface of the  
semiconductor chip;  
a plurality of connecting conductors connected to the  
surface of the semiconductor chip and penetrating the protective  
insulating layer to the outside surface of the protective  
10 insulating layer,  
wherein the connecting conductor includes a plurality of  
layers formed of same material and at least one of the layers  
is formed as a stress-absorbing layer having lower hardness  
than other layer.
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2. The semiconductor device according to claim 1, wherein  
said connecting conductor is formed from anisotropic conductive  
material.
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3. The semiconductor device according to claim 1, wherein  
said connecting conductor is formed from conductive material  
containing metal particles.
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4. The semiconductor device according to claim 1, wherein  
said connecting conductor is formed by means of stacking a  
plurality of layers in a staggered manner.

5. The semiconductor device according to claim 4, wherein  
said plurality of layers of the connecting conductor are formed  
in substantially identical diameter.

5 6. The semiconductor device according to claim 4, wherein  
said plurality of layers of the connecting conductor are formed  
in different diameters from each other in sequence of layers.

7. A semiconductor device comprising:  
10 a semiconductor chip,  
a protective insulating layer covering the surface of the  
semiconductor chip;  
a plurality of connecting conductors connected to the  
surface of the semiconductor chip and penetrating the protective  
insulating layer to the outside surface of the protective  
insulating layer;  
15 wherein the connecting conductor includes a plurality of  
layers formed of different material and at least one of the  
layers is formed as a stress-absorbing layer having lower  
hardness than other layer.  
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8. The semiconductor device according to claim 7, wherein  
said stress-absorbing layer is formed from gold or palladium.

25 9. The semiconductor device according to claim 7, wherein  
said stress-absorbing layer is formed from anisotropic  
conductive material.

10. The semiconductor device according to claim 7, wherein  
said stress-absorbing layer is formed from conductive material  
containing metal particles.

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11. The semiconductor device according to claim 7, wherein  
said connecting conductor is formed by means of stacking the  
plurality of layers in a staggered manner.

10           12. The semiconductor device according to claim 11,  
wherein said plurality of layers of the connecting conductor  
is formed in substantially identical diameter.

15           13. The semiconductor device according to claim 11,  
wherein said plurality of layers of the connecting conductor  
are formed in different diameters from each other in sequence  
of layers.